L Number	Hits	Search Text	DB	Time stamp
1	83	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20020724")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:24
2	67	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20010724")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:22
3	16	(((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20020724")) not (((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20010724"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:23
4	164	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) same (silicide or salicide or polycide or policide))) and (@ad < "20010724")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:25
5	209	((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) same (silicide or salicide or polycide or policide))) and (@ad < "20020724")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:25
6	146	(((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) same (silicide or salicide or polycide or policide))) and (@ad < "20020724")) not (((((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20020724"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 18:17
7	8	"6312993"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 18:17
8	3	(("6312993") or ("6215149") or ("6097061")).PN.	USPAT	2004/10/27 18:18
9	2	("6025237" | "6114065").PN.	USPAT	2004/10/27 18:18
10	3	6312993.URPN.	USPAT	2004/10/27 18:18
11	8	("5710438" | "5777370" | "5937315" | "5955770" | "5962904" | "5990528" | "6025620" | "6054744").PN.	USPAT	2004/10/27 18:19
12	5	6215149.URPN.	USPAT	2004/10/27 18:20
13	7	("5016067" | "5378655" | "5705415" | "5770878" | "5773343" | "5883399" | "5953602").PN.	USPAT	2004/10/27 18:20
14	6	6097061.URPN.	USPAT	2004/10/27 18:21
15	2797	((438/259) or (438/268) or (438/270) or (438/271)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 18:27
-	1	6707100.pn.	USPAT	2004/10/26 13:42
-	24	(("6479357") or ("6489204") or ("6509608") or ("6534367") or ("6465866") or ("6413822") or ("6476444") or ("6586800") or ("6252277") or ("6251730") or ("6051468") or ("5753554")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:15
-	198671	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:43

-	5850	trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:43
-	63833	silicide or salicide or polycide or policide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:43
-	98	((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 15:44
-	67	(((trench near2 ((mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) or gate)) and (silicide or salicide or polycide or policide)).ab.) and (@ad < "20010724")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 17:22